Please amend claim 10 as follows:

10. (Amended) A method of forming a silicon oxide layer comprising:

providing a semiconductor substrate having a stepped portion;

coating the semiconductor substrate with a spin-on glass (SOG) composition containing perhydropolysilazane having the compound formula -(SiH2NH)n- wheren n represents a positive integer, a weight average molecular weight within the range of from about 4,000 to about 8,000, a molecular weight dispersion within the range of about 3.0 to about 4.0, and a viscosity within the range of about 1 to about 10 mPa.s, at a shear rate within the range of about 54 to 420 (1/s), and

curing the SOG layer to form a layer of silicon oxide having a planar surface.

The changes in the previous claim are indicated below by brackets for deletions and underlining for insertions.

10. (Amended) A method of forming a silicon oxide layer comprising:

providing a semiconductor substrate having a stepped portion;

coating the semiconductor substrate with a spin-on glass (SOG) composition containing perhydropolysilazane having the compound formula -(SiH2NH)n- wheren n represents a positive integer, a weight average molecular weight within the range of from about 4,000 to about 8,000, and a molecular weight dispersion within the range of about 3.0 to about 4.0, and a viscosity within the range of about 1 to about 10 mPa.s, at a shear rate within the range of about 10 to 1,000 (1/s), and

curing the SOG layer to form a layer of silicon oxide having a planar surface.

Please amend claim 20 as follows:

20. (Amended) A method of forming a silicon oxide layer comprising:

providing a semiconductor substrate having a stepped portion;

forming a silicon nitride layer having a thickness within the range of from about 200 to about 600 Å on the semiconductor substrate;

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coating the semiconductor substrate and silicon nitride layer with a spin-on glass (SOG) composition containing perhydropolysilazane having the compound formula -(SiH2NH)n- wheren n represents a positive integer, a weight average molecular weight within the range of from about 4,000 to about 8,000, a molecular weight dispersion within the range of about 3.0 to about 4.0; and

curing the SOG layer to form a layer of silicon oxide having a planar surface.

The changes in the previous claim are indicated below by brackets for deletions and underlining for insertions.

20. (Amended) A [The] method [as claimed in claim 10, further comprising] of forming a silicon oxide layer comprising:

providing a semiconductor substrate having a stepped portion;

forming a silicon nitride layer having a thickness within the range of from about 200 to about 600 Å on the semiconductor substrate [before coating the spin-on glass composition];

coating the semiconductor substrate and silicon nitride layer with a spin-on glass (SOG) composition containing perhydropolysilazane having the compound formula -(SiH2NH)n- wheren n represents a positive integer, a weight average molecular weight within the range of from about 4,000 to about 8,000, a molecular weight dispersion within the range of about 3.0 to about 4.0; and

curing the SOG layer to form a layer of silicon oxide having a planar surface.

Please amend claim 23 as follows:

23. (Amended) A method of forming a silicon oxide layer comprising:

providing a semiconductor substrate having a stepped portion;

coating the semiconductor substrate with a spin-on glass (SOG) composition containing perhydropolysilazane having the compound formula -(SiH2NH)n- wheren n represents a positive integer, a weight average molecular weight within the range of from about 4,000 to about 8,000, a molecular weight dispersion within the range of about 3.0 to about 4.0, and

curing the SOG layer to form a layer of silicon oxide having a planar surface,

wherein the stepped portion is formed by:

partially etching an upper portion of the semiconductor substrate to form a trench; and

the silicon oxide layer is formed by:

coating the SOG composition on the substrate to fill the trench and to form an SOG layer; and

curing the SOG layer by:

pre-baking the SOG layer at a temperature within the range of from about 100 to about 500°C for a first period of time; and

main-baking the SOG layer at a temperature within the range of about 900 to about 1000 °C for a second period of time.

The changes in the previous claim are indicated below by brackets for deletions and underlining for insertions.

23. (Amended) A [The] method [as claimed in claim 10,] of forming a silicon oxide layer comprising:

providing a semiconductor substrate having a stepped portion;

coating the semiconductor substrate with a spin-on glass (SOG) composition containing perhydropolysilazane having the compound formula -(SiH2NH)n- wheren n represents a positive integer, a weight average molecular weight within the range of from about 4,000 to about 8,000, a molecular weight dispersion within the range of about 3.0 to about 4.0, and

curing the SOG layer to form a layer of silicon oxide having a planar surface,

wherein the stepped portion is formed by:

partially etching an upper portion of the semiconductor substrate to form a trench; and

the silicon oxide layer is formed by: [;]

coating the SOG composition on the substrate to fill the trench and to form an SOG layer; and

curing the SOG layer by:

pre-baking the SOG layer at a temperature within the range of from about 100 to about 500°C for a first period of time; and

main-baking the SOG layer at a temperature within the range of about 900 to about 1000 °C for a second period of time.

Please amend claim 25 as follows:

25. (Amended) A method of forming a silicon oxide layer comprising:

providing a semiconductor substrate having a stepped portion;

coating the semiconductor substrate with a spin-on glass (SOG) composition containing perhydropolysilazane having the compound formula -(SiH2NH)n- wheren n represents a positive integer, a weight average molecular weight within the range of from about 4,000 to about 8,000, a molecular weight dispersion within the range of about 3.0 to about 4.0, and

curing the SOG layer to form a layer of silicon oxide having a planar surface,

wherein the stepped portion is formed by:

forming a plurality of gate electrodes on the semiconductor substrate;

and the silicon oxide layer is formed by:

coating the SOG composition on the substrate to completely cover the plurality of gate electrodes and to form an SOG layer; and

curing the SOG layer by:

pre-baking the SOG layer at a temperature within the range of from about 100 to about 500°C for a first period of time; and

main-baking the SOG layer at a temperature within the range of about 900 to about 1000 °C for a second period of time.

The changes in the previous claim are indicated below by brackets for deletions and underlining for insertions.

25. (Amended) A [The] method [as claimed in claim 10,] of forming a silicon oxide layer comprising:

providing a semiconductor substrate having a stepped portion;

coating the semiconductor substrate with a spin-on glass (SOG) composition containing perhydropolysilazane having the compound formula -(SiH2NH)n- wheren n represents a positive integer, a weight average molecular weight within the range of from about 4,000 to about 8,000, a molecular weight dispersion within the range of about 3.0 to about 4.0, and

curing the SOG layer to form a layer of silicon oxide having a planar surface,

wherein the stepped portion is formed by:

forming a plurality of gate electrodes on the semiconductor substrate;

and the silicon oxide layer is formed by: [:]

coating [a] the SOG composition on the substrate to completely cover the plurality of gate electrodes and to form an SOG layer; and

curing the SOG layer by:

pre-baking the SOG layer at a temperature within the range of from about 100 to about 500°C for a first period of time; and

main-baking the SOG layer at a temperature within the range of about 900 to about 1000 °C for a second period of time.

Please amend claim 27 as follows:

27. (Amended) A method of forming a silicon oxide layer comprising:

providing a semiconductor substrate having a stepped portion;

coating the semiconductor substrate with a spin-on glass (SOG) composition containing perhydropolysilazane having the compound formula -(SiH2NH)n- wheren n represents a positive integer, a weight average molecular weight within the range of from about 4,000 to about 8,000, a molecular weight dispersion within the range of about 3.0 to about 4.0, and

curing the SOG layer to form a layer of silicon oxide having a planar surface,

wherein the stepped portion is formed by:

forming an insulation layer on the semiconductor substrate; and

forming a plurality of metal wiring patterns on the insulation layer;

and the silicon oxide layer is formed by:

coating the SOG composition on the substrate to completely cover the metal wiring patterns thereby to form an SOG layer; and

curing the SOG layer by:

pre-baking the SOG layer at a temperature within the range of from about 100 to about 500°C for a first period of time; and

main-baking the SOG layer at a temperature within the range of about 900 to about 1000 °C for a second period of time.

The changes in the previous claim are indicated below by brackets for deletions and underlining for insertions.

27. (Amended) A [The] method [as claimed in claim 10,] of forming a silicon oxide layer comprising:

providing a semiconductor substrate having a stepped portion;

coating the semiconductor substrate with a spin-on glass (SOG) composition containing perhydropolysilazane having the compound formula -(SiH2NH)n- wheren n represents a positive integer, a weight average molecular weight within the range of from about 4,000 to about 8,000, a molecular weight dispersion within the range of about 3.0 to about 4.0, and

curing the SOG layer to form a layer of silicon oxide having a planar surface,

wherein the stepped portion is formed by:

forming an insulation layer on the semiconductor substrate; and

forming a plurality of metal wiring patterns on the insulation layer;

and the silicon oxide layer is formed by: [:]

coating [a] the SOG composition on the substrate to completely cover the metal wiring patterns thereby to form an SOG layer; and

curing the SOG layer by:

pre-baking the SOG layer at a temperature within the range of from about 100 to about 500°C for a first period of time; and

main-baking the SOG layer at a temperature within the range of about 900 to about 1000 °C for a second period of time.